

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A film deposition apparatus comprising:

a stock chamber for loading or unloading a substrate;

a transferring chamber including a first mechanism for transferring said substrate; and

a liquid phase film deposition chamber connected to said transferring chamber through a gate,

wherein said liquid phase film deposition chamber is provided with a second mechanism for oxidizing an element belonging to Group 1 or 2 of the periodic table,

wherein said second mechanism includes an oxidization cell having a lid for controlling a time of the oxidization and an oxygen gettering agent.

2. (Original) A film deposition apparatus according to claim 1,

wherein an inside of said transferring chamber is kept under a reduced pressure and said liquid phase film deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

3. (Original) A film deposition apparatus according to claim 1,

wherein said transferring chamber is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

4. (Currently Amended) A film deposition apparatus comprising:
a stock chamber for loading or unloading a substrate;
a transferring chamber including a first mechanism for transferring the substrate; and
a liquid phase film deposition chamber connected to said transferring chamber through a gate,

wherein said liquid phase film deposition chamber is provided with, via a piping, a second mechanism for oxidizing an element belonging to Group 1 or 2 of the periodic table,

wherein said second mechanism includes an oxidization cell having a lid for controlling a time of the oxidization and an oxygen gettering agent.

5. (Original) A film deposition apparatus according to claim 4,
wherein an inside of said transferring chamber is kept under a reduced pressure and said liquid phase film deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

6. (Original) A film deposition apparatus according to claim 4,
wherein said transferring chamber is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

7. (Currently Amended) A film deposition apparatus comprising:
a stock chamber for loading or unloading a substrate;
two transferring chambers each connected to said stock chamber through a gate;

a vapor phase film deposition chamber connected to one of said two transferring chambers through a gate; and

a liquid phase film deposition chamber connected to another said transferring chamber through a gate,

wherein said liquid phase film deposition chamber is provided with a mechanism for oxidizing an element belonging to Group 1 or 2 of the periodic table,

wherein said second mechanism includes an oxidization cell having a lid for controlling a time of the oxidization and an oxygen gettering agent.

8. (Previously presented) A film deposition apparatus according to claim 7,

wherein an inside of one of said transferring chambers is kept under a reduced pressure and said liquid phase film deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

9. (Previously presented) A film deposition apparatus according to claim 7,

wherein one of said transferring chambers is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

10 (Currently Amended). A film deposition apparatus comprising:

a stock chamber for loading or unloading a substrate;

two transferring chambers each connected to said stock chamber through a gate;

a vapor phase film deposition chamber connected to one of said two transferring chambers through a gate; and

a liquid phase film deposition chamber connected to another said transferring chamber through a gate,

wherein said liquid phase film deposition chamber is provided with, via a piping, a mechanism for oxidizing an element belonging to Group 1 or 2 of the periodic table,

wherein said second mechanism includes an oxidization cell having a lid for controlling a time of the oxidization and an oxygen gettering agent.

11. (Previously presented) A film deposition apparatus according to claim 10,
wherein an inside of one of said transferring chambers is kept under a reduced pressure and said liquid phase film deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

12. (Previously presented) A film deposition apparatus according to claim 10,
wherein one of said transferring chambers is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

13. (Currently Amended) A film deposition apparatus comprising:

a stock chamber for loading or unloading a substrata;

a transferring chamber for transferring said substrate; and

an EL material deposition chamber connected to said transferring chamber through a gate,

wherein said EL material deposition chamber is provided with a cell which contains an element belonging to Group 1 or 2 of the periodic table,

wherein said second mechanism includes an oxidization cell having a lid for controlling a time of the oxidization and an oxygen gettering agent.

14. (Original) A film deposition apparatus according to claim 13,

wherein an inside of said transferring chamber is kept under a reduced pressure and said EL material deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

15. (Original) A film deposition apparatus according to claim 13,

wherein said transferring chamber is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

16. (Currently Amended) A film deposition apparatus comprising:

a stock chamber for loading or unloading a substrate;

two transferring chambers each connected to said stock chamber through a gate;

a vapor phase film deposition chamber connected to one of said two transferring chambers through a gate; and

an EL material deposition chamber connected to another said transferring chamber through a gate,

wherein said EL material deposition chamber is provided with a cell which contains an element belonging to Group 1 or 2 of the periodic table,

wherein said second mechanism includes an oxidization cell having a lid for controlling a time of the oxidization and an oxygen gettering agent.

17. (Previously presented) A film deposition apparatus according to claim 16,
wherein an inside of one of said transferring chambers is kept under a reduced pressure and said EL material deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

18. (Previously presented) A film deposition apparatus according to claim 16,
wherein one of said transferring chambers is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

19-30 (Cancelled).

31 (Previously presented) A film deposition apparatus according to claim 1,
wherein said liquid phase film deposition chamber is a chamber for depositing an EL material.

32 (Previously presented) A film deposition apparatus according to claim 1,
wherein said liquid phase film deposition chamber is provided with a spin coater for forming an EL layer.

33 (Previously presented) A film deposition apparatus according to claim 1,
wherein said liquid phase film deposition chamber is provided with a nozzle for forming an
EL layer.

34 (Previously presented) A film deposition apparatus according to claim 4,
wherein said liquid phase film deposition chamber is a chamber for depositing an EL
material.

35 (Previously presented) A film deposition apparatus according to claim 4,
wherein said liquid phase film deposition chamber is provided with a spin coater for
forming an EL layer.

36 (Previously presented) A film deposition apparatus according to claim 4,
wherein said liquid phase film deposition chamber is provided with a nozzle for forming an
EL layer.

37 (Previously presented) A film deposition apparatus according to claim 7,
wherein said liquid phase film deposition chamber is a chamber for depositing an EL
material.

38 (Previously presented) A film deposition apparatus according to claim 7,
wherein said liquid phase film deposition chamber is provided with a spin coater for
forming an EL layer.

39 (Previously presented) A film deposition apparatus according to claim 7,
wherein said liquid phase film deposition chamber is provided with a nozzle for forming an
EL layer.

40 (Previously presented) A film deposition apparatus according to claim 10,
wherein said liquid phase film deposition chamber is a chamber for depositing an EL
material.

41 (Previously presented) A film deposition apparatus according to claim 10,
wherein said liquid phase film deposition chamber is provided with a spin coater for
forming an EL layer.

42 (Previously presented) A film deposition apparatus according to claim 10,
wherein said liquid phase film deposition chamber is provided with a nozzle for forming an
EL layer.

43 (Previously presented) A film deposition apparatus according to claim 13,
wherein said EL material deposition chamber is provided with a spin coater for forming an
EL layer.

44 (Previously presented) A film deposition apparatus according to claim 13,

wherein said EL material deposition chamber is provided with a nozzle for forming an EL layer.

45 (Previously presented) A film deposition apparatus according to claim 16, wherein said EL material deposition chamber is provided with a spin coater for forming an EL layer.

46 (Previously presented) A film deposition apparatus according to claim 16, wherein said EL material deposition chamber is provided with a nozzle for forming an EL layer.

47 (Previously presented) A film deposition apparatus according to claim 1, wherein said lid is opened and closed.

48 (Previously presented) A film deposition apparatus according to claim 4, wherein said lid is opened and closed.

49 (Previously presented) A film deposition apparatus according to claim 7, wherein said lid is opened and closed.

50 (Previously presented) A film deposition apparatus according to claim 10, wherein said lid is opened and closed.

51 (Previously presented) A film deposition apparatus according to claim 13,
wherein said lid is opened and closed.

52 (Previously presented) A film deposition apparatus according to claim 16,
wherein said lid is opened and closed.

53 (New) A film deposition apparatus according to claim 1,
wherein said second mechanism includes a heater.

54 (New) A film deposition apparatus according to claim 4,
wherein said second mechanism includes a heater.

55 (New) A film deposition apparatus according to claim 7,
wherein said second mechanism includes a heater.

56 (New) A film deposition apparatus according to claim 10,
wherein said second mechanism includes a heater.

57 (New) A film deposition apparatus according to claim 13,
wherein said second mechanism includes a heater.

58 (New) A film deposition apparatus according to claim 16,
wherein said second mechanism includes a heater.